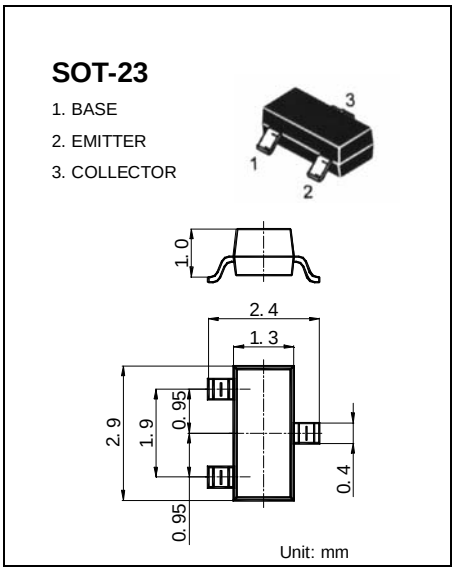
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Transistors

S9018LT1 TRANSISTOR (NPN)



FEATURES

Power dissipation

$P_{CM:}$ 0.2 W (Tamb=25℃)

Collector current

$I_{CM:}$ 0.05 A

Collector-base voltage

$V_{(BR)CBO}$: 25 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= 100μA, I_E=0	25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= 0.1mA, I_B=0	18			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	4			V
Collector cut-off current	I_{CBO}	V_{CB}=20V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=15V, I_B=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 3V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=5V, I_C= 1mA	70		190	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10mA, I_B= 1mA			0.5	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=10mA, I_B= 1mA			1.4	V
Transition frequency	f_T	V_{CE}=5V, I_C= 5mA f=400MHz	600			MHz

DEVICE MARKING	**S9018LT1= J8**